Please amend the paragraph beginning on page 54, line 23, and continuing to page 55, line 3, as follows:

The chips used in FIG's. 29(a) and 29(b) have the [natures] nature described with reference to FIG's. 27 and 28 and are arbitrarily selected from a plurality of chips simultaneously formed on a semiconductor wafer. The chips to be compared with each other depend upon a case. However, it is general that the chips are adjacent ones or that the test is performed by selecting a specific chip, which may be a normal chip, as the first sample, with sequentially changing other chips as the second sample. It may be possible to compare test results of three chips or more and determine a chip or chips, whose test results indicate many coincidences with those of the specific chip, as normal chips.

In the Claims:

Please amend the claims as follows. A clean copy of the amended claims is attached.

Claim 1 (Amended). A semiconductor device tester comprising:

electron beam irradiation means for irradiating a semiconductor device as a sample under test with an electron beam while scanning the semiconductor device;

a current measuring means for measuring current flowing through the semiconductor resulting from [by] irradiation by the electron beam; and

data processing means for processing measured data from said current measuring means,

wherein said electron beam irradiation means includes collimator means for collimating the electron beam to a parallel beam and means for changing an acceleration voltage of the electron beam and wherein said data processing means includes means for obtaining an information related to a structure of the sample in a depth direction on the basis of a difference

in transmittivity of the electron beam for the sample when the latter is scanned with different acceleration voltages.

Claim 4 (Amended). A semiconductor device tester as claimed in claim 1, wherein said electron beam irradiating means includes means for vertically irradiating said sample along a line segment passing through a center of a measuring region of said sample with an electron beam having spot size smaller than an area of said measuring region and said data processing means includes means for obtaining a distance of a bottom of said measuring region from a space between [a] rising and following edges of a current measured along said line segment.

Claim 9 (Amended). A semiconductor device tester as claimed in claim 1, wherein said data processing means includes means for comparing a current [vale] value measured correspondingly to a positional coordinates when a wafer under test is irradiated with an electron beam with a current value to be measured at the same positional coordinates of the wafer is good and setting the kind of process to be performed next on the basis of the result of the comparison.

withdrawn

REMARKS

This application claims benefit of priority under 35 U.S.C. §119 based on Japanese applications 11-315320 filed November 5, 1999, 2000-191817 filed June 26, 2000, and 2000-311196 filed October 11, 2000. The priority documents were filed on February 12, 2001. Acknowledgment of the claim of priority and receipt of the priority documents is respectfully requested.

The specification has been carefully reviewed and amended as appropriate to correct minor typographical, grammatical and spelling errors. No new matter has been added.